



P-Channel and P-Channel Complementary MOSFET

Product Summary

V_{DS}	-30 V
I_D	-5.1 A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	43 m
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	59 m

General Description

High density cell design for low $R_{DS(ON)}$
High Speed switching
Moisture Sensitivity Level 3
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Wireless charger
Load switch
Power management

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter





Typical Electrical and Thermal Characteristics Diagrams

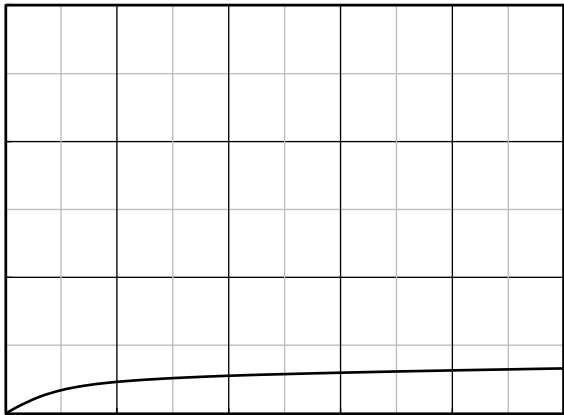




Figure 7. $R_{DS(on)}$ VS Drain Current

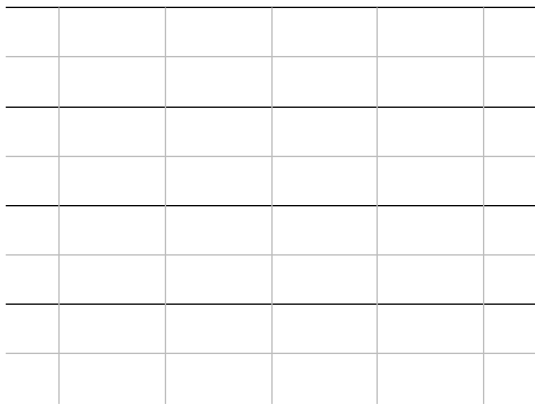


Figure 8. Forward characteristics of reverse diode

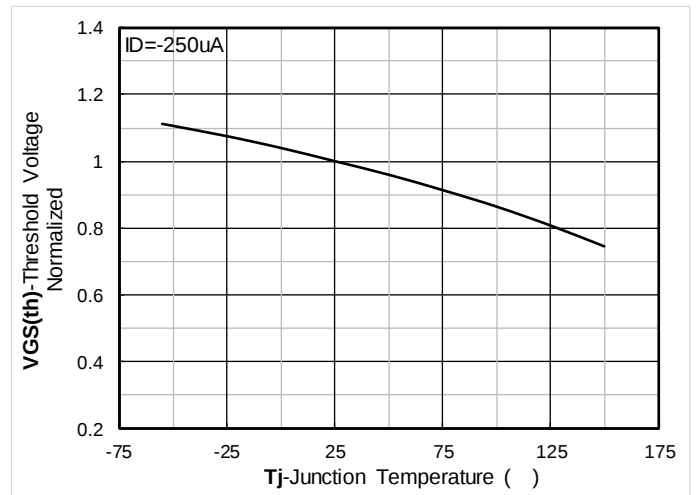


Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage

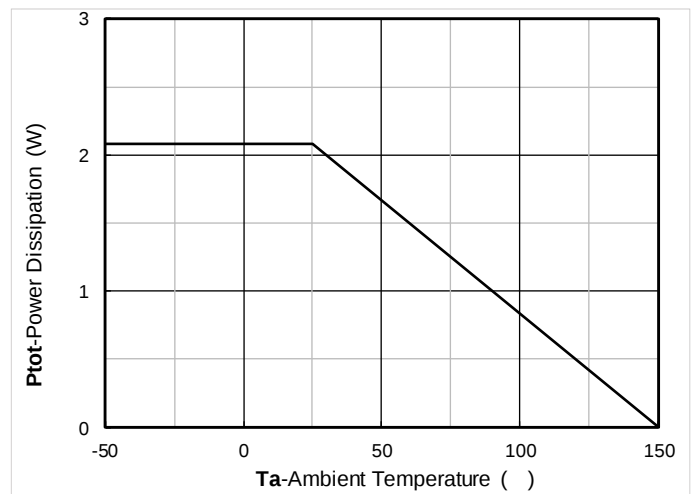
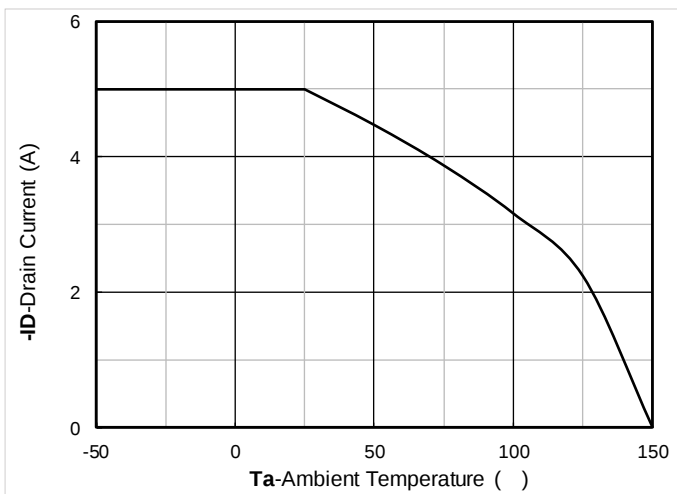


Figure 11. Current dissipation

Figure 12. Power dissipation

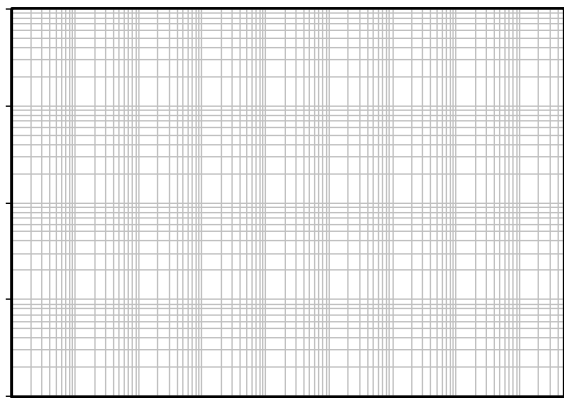


Figure 13. Maximum Transient Thermal Impedance

Figure 14



SOP-8 Package information

SYMBOL	MIN.		
	0.053	0.069	
B	0.004	0.010	
		0.061	
D		0.020	
E			
F			
G	0.050BSC		1.270BSC
H			
J			
K			

